Michael Jetter

List of Publications by Year in Descending Order

187	2,689	28	42
papers	citations	h-index	g-index
229	3,218	3.5	4.91
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
187	Optical charge injection and coherent control of a quantum-dot spin-qubit emitting at telecom wavelengths.. *Nature Communications*, **2022**, 13, 748	17.4	1
186	Non-equilibrium spin noise spectroscopy of a single quantum dot operating at fiber telecommunication wavelengths. *Journal of Applied Physics*, **2022**, 131, 065703	2.5	
185	High-power quasi-CW diode-pumped 750-nm AlGaAs VECSEL emitting a peak power of 29.6 W and an average power of 8.5 W.. *Optics Letters*, **2022**, 47, 1980-1983	3	1
184	Achieving stable fiber coupling of quantum dot telecom C-band single-photons to an SOI photonic device. *Applied Physics Letters*, **2021**, 119, 211101	3.4	1
183	Resonance fluorescence of single In(Ga)As quantum dots emitting in the telecom C-band. *Applied Physics Letters*, **2021**, 118, 244002	3.4	3
182	3D printed micro-optics for quantum technology: Optimised coupling of single quantum dot emission into a single-mode fibre. *Light Advanced Manufacturing*, **2021**, 2, 1-17	1	5
181	Microcavity-enhanced Kerr nonlinearity in a vertical-external-cavity surface-emitting laser: erratum. *Optics Express*, **2021**, 29, 23290-23291	3.3	0
180	Optically Pumped Red-Emitting AlGaInP-VECSELs and the MECSEL Concept **2021**, 197-228		
179	Single-frequency and High Power Operation of 2□ Micron VECSEL **2021**, 63-107		1
178	Mode-Locked AlGaInP VECSEL for the Red and UV Spectral Range **2021**, 305-320		
177	VECSELs in the Wavelength Range 1.18□1.55 □h **2021**, 27-62		
176	Self-Mode-Locked Semiconductor Disk Lasers **2021**, 357-385		
175	Bright Purcell Enhanced Single-Photon Source in the Telecom O-Band Based on a Quantum Dot in a Circular Bragg Grating. *Nano Letters*, **2021**, 21, 7740-7745	11.5	7
174	DBR -free Optically Pumped Semiconductor Disk Lasers **2021**, 175-196		1
173	Recent Advances in Mode-Locked Vertical-External-Cavity Surface-Emitting Lasers **2021**, 229-266		
172	Stable fundamental and dual-pulse mode locking of red-emitting VECSELs. *Laser Physics Letters*, **2020**, 17, 065001	1.5	2
171	Characterization of spectral diffusion by slow-light photon-correlation spectroscopy. *Physical Review B*, **2020**, 101,	3.3	4

170	Quantum dot-based broadband optical antenna for efficient extraction of single photons in the telecom O-band. *Optics Express*, **2020**, 28, 19457-19468	3.3	6
169	Gaussian-like transverse-mode profile characteristics of high-power large-area red-emitting VCSELs. *Optics Letters*, **2020**, 45, 1419-1422	3	1
168	Realization of a tunable fiber-based double cavity system. *Physical Review B*, **2020**, 102,	3.3	3
167	Purcell-enhanced single-photon emission from a strain-tunable quantum dot in a cavity-waveguide device. *Applied Physics Letters*, **2020**, 117, 254002	3.4	5
166	Controllable Delay and Polarization Routing of Single Photons. *Advanced Quantum Technologies*, **2020**, 3, 1900057	4.3	2
165	Wavelength and Pump-Power Dependent Nonlinear Refraction and Absorption in a Semiconductor Disk Laser. *IEEE Photonics Technology Letters*, **2020**, 32, 85-88	2.2	2
164	Tuning emission energy and fine structure splitting in quantum dots emitting in the telecom O-band. *AIP Advances*, **2019**, 9, 085112	1.5	5
163	Deterministic fabrication of circular Bragg gratings coupled to single quantum emitters via the combination of in-situ optical lithography and electron-beam lithography. *Journal of Applied Physics* , **2019**, 125, 045701	2.5	20
162	Optical Gain and Lasing Properties of InP/AlGaInP Quantum-Dot Laser Diode Emitting at 660 nm. *IEEE Journal of Quantum Electronics*, **2019**, 55, 1-7	2	9
161	Single-photon light-emitting diodes based on preselected quantum dots using a deterministic lithography technique. *Applied Physics Letters*, **2019**, 114, 222101	3.4	4
160	Characterization of a Photon-Number Resolving SNSPD Using Poissonian and Sub-Poissonian Light. *IEEE Transactions on Applied Superconductivity*, **2019**, 29, 1-5	1.8	7
159	InAs quantum dots grown on metamorphic buffers as non-classical light sources at telecom C-band: a review. *Semiconductor Science and Technology*, **2019**, 34, 053001	1.8	23
158	Coherence and indistinguishability of highly pure single photons from non-resonantly and resonantly excited telecom C-band quantum dots. *Applied Physics Letters*, **2019**, 115, 023103	3.4	21
157	Semiconductor Quantum Dots for Integrated Quantum Photonics. *Advanced Quantum Technologies* , **2019**, 2, 1900020	4.3	29
156	Semiconductor Quantum Dots for Integrated Quantum Photonics (Adv. Quantum Technol. 9/2019). *Advanced Quantum Technologies*, **2019**, 2, 1970053	4.3	3
155	Microcavity-enhanced Kerr nonlinearity in a vertical-external-cavity surface-emitting laser. *Optics Express*, **2019**, 27, 11914-11929	3.3	12
154	Two-photon interference in the telecom C-band after frequency conversion of photons from remote quantum emitters. *Nature Nanotechnology*, **2019**, 14, 23-26	28.7	50
153	Signatures of single-photon interaction between two quantum dots located in different cavities of a weakly coupled double microdisk structure. *Physical Review B*, **2018**, 97,	3.3	5

152	Two-photon interference in an atom□quantum dot hybrid system. *Optica*, **2018**, 5, 367	8.6	21
151	Deterministic integration and optical characterization of telecom O-band quantum dots embedded into wet-chemically etched Gaussian-shaped microlenses. *Applied Physics Letters*, **2018**, 113, 032103	3.4	24
150	Single-photon and polarization-entangled photon emission from InAs quantum dots in the telecom C-band **2018**,		1
149	Bragg grating cavities embedded into nano-photonic waveguides for Purcell enhanced quantum dot emission. *Optics Express*, **2018**, 26, 30614-30622	3.3	11
148	Chem/bio sensing with non-classical light and integrated photonics. *Analyst, The*, **2018**, 143, 593-605	5	11
147	Fully On-Chip Single-Photon Hanbury-Brown and Twiss Experiment on a Monolithic Semiconductor-Superconductor Platform. *Nano Letters*, **2018**, 18, 6892-6897	11.5	42
146	Structural and optical properties of InAs/(In)GaAs/GaAs quantum dots with single-photon emission in the telecom C-band up to 77 K. *Physical Review B*, **2018**, 98,	3.3	28
145	Overcoming correlation fluctuations in two-photon interference experiments with differently bright and independently blinking remote quantum emitters. *Physical Review B*, **2018**, 97,	3.3	10
144	Pure single-photon emission from In(Ga)As QDs in a tunable fiber-based external mirror microcavity. *Quantum Science and Technology*, **2018**, 3, 034009	5.5	9
143	Combining in-situ lithography with 3D printed solid immersion lenses for single quantum dot spectroscopy. *Scientific Reports*, **2017**, 7, 39916	4.9	42
142	The optically pumped semiconductor membrane external-cavity surface-emitting laser (MECSEL): a concept based on a diamond-sandwiched active region **2017**,		1
141	Temperature-dependent properties of single long-wavelength InGaAs quantum dots embedded in a strain reducing layer. *Journal of Applied Physics*, **2017**, 121, 184302	2.5	13
140	Polarization-entangled photons from an InGaAs-based quantum dot emitting in the telecom C-band. *Applied Physics Letters*, **2017**, 111, 133106	3.4	43
139	Single-photon emission at 1.55 □m from MOVPE-grown InAs quantum dots on InGaAs/GaAs metamorphic buffers. *Applied Physics Letters*, **2017**, 111, 033102	3.4	63
138	Self-mode-locked AlGaInP-VECSEL. *Applied Physics Letters*, **2017**, 111, 182105	3.4	6
137	Quantitative STEM: Comparative Studies of Composition and Optical Properties of Semiconductor Quantum Structures. *Microscopy and Microanalysis*, **2017**, 23, 1690-1691	0.5	
136	DBR-free semiconductor disc laser on SiC heatspreader emitting 10.1 W at 1007□hm. *Electronics Letters*, **2017**, 53, 1537-1539	1.1	15
135	Photonic Integrated Circuits with Quantum Dots. *Nano-optics and Nanophotonics*, **2017**, 409-441	0	

134	Neutral and charged biexciton-exciton cascade in near-telecom-wavelength quantum dots. *Physical Review B*, **2016**, 94,	3.3	17
133	Generation, guiding and splitting of triggered single photons from a resonantly excited quantum dot in a photonic circuit. *Optics Express*, **2016**, 24, 3089-94	3.3	27
132	Efficiency and power scaling of in-well and multi-pass pumped AlGaInP VECSELs **2016**,		2
131	2.5 W continuous wave output at 665 nm from a multipass and quantum-well-pumped AlGaInP vertical-external-cavity surface-emitting laser. *Optics Letters*, **2016**, 41, 1245-8	3	16
130	Single-photon and photon pair emission from MOVPE-grown In(Ga)As quantum dots: shifting the emission wavelength from 1.0 to 1.3 □m. *Applied Physics B: Lasers and Optics*, **2016**, 122, 1	1.9	13
129	Gain chip design, power scaling and intra-cavity frequency doubling with LBO of optically pumped red-emitting AlGaInP-VECSELs **2016**,		2
128	Low-noise quantum frequency down-conversion of indistinguishable photons. *Optics Express*, **2016**, 24, 22250-60	3.3	19
127	Semiconductor membrane external-cavity surface-emitting laser (MECSEL). *Optica*, **2016**, 3, 1506	8.6	31
126	Simultaneous Faraday filtering of the Mollow triplet sidebands with the Cs-D clock transition. *Nature Communications*, **2016**, 7, 13632	17.4	27
125	Mid-Infrared Spectroscopy Platform Based on GaAs/AlGaAs Thin-Film Waveguides and Quantum Cascade Lasers. *Analytical Chemistry*, **2016**, 88, 2558-62	7.8	35
124	Quantitative measurements of internal electric fields with differential phase contrast microscopy on InGaN/GaN quantum well structures. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 140-144	1.3	26
123	Defect reduced selectively grown GaN pyramids as template for green InGaN quantum wells. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 67-72	1.3	1
122	Monolithic on-chip integration of semiconductor waveguides, beamsplitters and single-photon sources. *Journal Physics D: Applied Physics*, **2015**, 48, 085101	3	31
121	Quantum dot based mode-locked AlGaInP-VECSEL **2015**,		3
120	Fabrication and optical characterization of large scale membrane containing InP/AlGaInP quantum dots. *Nanotechnology*, **2015**, 26, 235201	3.4	1
119	Enhanced efficiency of AlGaInP disk laser by in-well pumping. *Optics Express*, **2015**, 23, 2472-86	3.3	13
118	Intra-cavity frequency-doubled mode-locked semiconductor disk laser at 325 nm. *Optics Express*, **2015**, 23, 19947-53	3.3	14
117	Metal-organic vapor-phase epitaxy-grown ultra-low density InGaAs/GaAs quantum dots exhibiting cascaded single-photon emission at 1.3 □m. *Applied Physics Letters*, **2015**, 106, 122105	3.4	32

116	On-chip beamsplitter operation on single photons from quasi-resonantly excited quantum dots embedded in GaAs rib waveguides. *Applied Physics Letters*, **2015**, 107, 021101	3.4	27
115	Comparison of AlGaInP-VECSEL gain structures. *Journal of Crystal Growth*, **2015**, 414, 219-222	1.6	6
114	All quantum dot mode-locked semiconductor disk laser emitting at 655 nm. *Applied Physics Letters*, **2014**, 105, 082107	3.4	13
113	Active and Passive LC Based Polarization Elements. *Molecular Crystals and Liquid Crystals*, **2014**, 594, 140-149	0.5	3
112	Spectroscopy of the D1 transition of cesium by dressed-state resonance fluorescence from a single (In,Ga)As/GaAs quantum dot. *Physical Review B*, **2014**, 90,	3.3	18
111	Structural and emission properties of InGaAs/GaAs quantum dots emitting at 1.3 Ħh. *Applied Physics Letters*, **2014**, 105, 152102	3.4	19
110	Femtosecond mode-locked red AlGaInP-VECSEL **2014**,		2
109	High optical output power in the UVA range of a frequency-doubled, strain-compensated AlGaInP-VECSEL. *Applied Physics Express*, **2014**, 7, 092705	2.4	15
108	Strain compensation techniques for red AlGaInP-VECSELs: Performance comparison of epitaxial designs. *Journal of Crystal Growth*, **2013**, 370, 208-211	1.6	8
107	Influence of the oxide aperture radius on the mode spectra of (Al,Ga)As vertical microcavities with electrically excited InP quantum dots. *Applied Physics Letters*, **2013**, 102, 011132	3.4	3
106	High-power InP quantum dot based semiconductor disk laser exceeding 1.3 W. *Applied Physics Letters*, **2013**, 102, 092101	3.4	24
105	Red Emitting VCSEL. *Springer Series in Optical Sciences*, **2013**, 379-401	0.5	
104	Mode-locked red-emitting semiconductor disk laser with sub-250 fs pulses. *Applied Physics Letters*, **2013**, 103, 242101	3.4	28
103	Site-controlled growth of InP/GaInP islands on periodic hole patterns in GaAs substrates produced by microsphere photolithography. *Journal of Crystal Growth*, **2013**, 370, 146-149	1.6	4
102	Detuning-dependent Mollow triplet of a coherently-driven single quantum dot. *Optics Express*, **2013**, 21, 4382-95	3.3	87
101	Mollow quintuplets from coherently excited quantum dots. *Optics Letters*, **2013**, 38, 1691-3	3	14
100	Strong mode coupling in InP quantum dot-based GaInP microdisk cavity dimers. *New Journal of Physics*, **2013**, 15, 013060	2.9	9
99	Postselected indistinguishable single-photon emission from the Mollow triplet sidebands of a resonantly excited quantum dot. *Physical Review B*, **2013**, 87,	3.3	13

98	Electrically driven quantum dot single-photon source at 2 GHz excitation repetition rate with ultra-low emission time jitter. *Applied Physics Letters*, **2013**, 102, 011126	3.4	45
97	Differential phase contrast 2.0--opening new "fields" for an established technique. *Ultramicroscopy*, **2012**, 117, 7-14	3.1	72
96	Reducing vortex losses in superconducting microwave resonators with microsphere patterned antidot arrays. *Applied Physics Letters*, **2012**, 100, 012601	3.4	33
95	Ultra-sensitive mid-infrared evanescent field sensors combining thin-film strip waveguides with quantum cascade lasers. *Analyst, The*, **2012**, 137, 2322-7	5	60
94	Cascaded single-photon emission from the Mollow triplet sidebands of a quantum dot. *Nature Photonics*, **2012**, 6, 238-242	33.9	98
93	Strong antibunching from electrically driven devices with long pulses: A regime for quantum-dot single-photon generation. *Physical Review B*, **2012**, 86,	3.3	9
92	Visible-to-telecom quantum frequency conversion of light from a single quantum emitter. *Physical Review Letters*, **2012**, 109, 147404	7.4	159
91	Quantum key distribution using quantum dot single-photon emitting diodes in the red and near infrared spectral range. *New Journal of Physics*, **2012**, 14, 083001	2.9	63
90	Single-photon emission from electrically driven InP quantum dots epitaxially grown on CMOS-compatible Si(001). *Nanotechnology*, **2012**, 23, 335201	3.4	9
89	Red AlGaInP-VECSEL emitting at around 665 nm: strain compensation and performance comparison of different epitaxial designs **2012**,		4
88	Phonon-assisted incoherent excitation of a quantum dot and its emission properties. *Physical Review B*, **2012**, 86,	3.3	52
87	Excited-state spectroscopy of single lateral self-assembled InGaAs quantum dot molecules. *Physical Review B*, **2012**, 85,	3.3	7
86	Epitaxially Grown Indium Phosphide Quantum Dots on a Virtual Ge Substrate Realized on Si(001). *Applied Physics Express*, **2012**, 5, 042001	2.4	1
85	Vertically stacked and laterally ordered InP and In(Ga)As quantum dots for quantum gate applications. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 737-746	1.3	8
84	Optical investigations on single vertically coupled InP/GaInP quantum dot pairs. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 747-751	1.3	5
83	The phase boundary of superconducting niobium thin films with antidot arrays fabricated with microsphere photolithography. *Superconductor Science and Technology*, **2012**, 25, 065020	3.1	5
82	Transverse mode and polarization characteristics of AlGaInP-based VCSELs with integrated multiple oxide apertures **2012**,		1
81	Electron and hole spins in InP/(Ga,In)P self-assembled quantum dots. *Physical Review B*, **2012**, 86,	3.3	9

80	Frequency doubled AlGaInP-VECSEL with high output power at 331 nm and a large wavelength tuning range in the UV **2012**,		2
79	UV laser emission around 330 nm via intracavity frequency doubling of a tunable red AlGaInP-VECSEL **2012**,		1
78	Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. *Microscopy and Microanalysis*, **2012**, 18, 1838-1839	0.5	1
77	Lasing properties of InP/(Ga0.51In0.49)P quantum dots in microdisk cavities. *Physical Review B*, **2011**, 83,	3.3	24
76	Wavelength tunable red AlGaInP-VECSEL emitting at around 660 nm **2011**,		2
75	Transverse-Mode Analysis of Red-Emitting Highly Polarized Vertical-Cavity Surface-Emitting Lasers. *IEEE Journal of Selected Topics in Quantum Electronics*, **2011**, 17, 724-729	3.8	8
74	Short wavelength red-emitting AlGaInP-VECSEL exceeds 1.2 W continuous-wave output power. *Applied Physics B: Lasers and Optics*, **2011**, 102, 789-794	1.9	21
73	Growth and characterization of electrically pumped red-emitting VCSEL with embedded InP/AlGaInP quantumdots. *Journal of Crystal Growth*, **2011**, 315, 131-133	1.6	3
72	Quaternary AlxInyGa1□□N layers deposited by pulsed metal-organic vapor-phase epitaxy for high efficiency light emission. *Journal of Crystal Growth*, **2011**, 315, 254-257	1.6	9
71	Three-dimensional GaN for semipolar light emitters. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 549-560	1.3	55
70	High wavelength tunability of InGaN quantum wells grown on semipolar GaN pyramid facets. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 605-610	1.3	16
69	Spectrally and time-resolved cathodoluminescence microscopy of semipolar InGaN SQW on (11$overline {2} $2) and (10$overline {1} $1) pyramid facets. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 632-637	1.3	10
68	MOVPE grown quaternary AlInGaN layers for polarization matched quantum wells and efficient active regions. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2163-2166		3
67	Spectral features in different sized InGaN/GaN micropyramids. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2387-2389		2
66	InP/AlGaInP quantum dot laser emitting at 638 nm. *Journal of Crystal Growth*, **2011**, 315, 123-126	1.6	41
65	Pulsed single-photon resonant-cavity quantum dot LED. *Journal of Crystal Growth*, **2011**, 315, 127-130	1.6	6
64	Wavelength tunable ultraviolet laser emission via intra-cavity frequency doubling of an AlGaInP vertical external-cavity surface-emitting laser down to 328 nm. *Applied Physics Letters*, **2011**, 99, 261101	3.4	18
63	Triggered single-photon emission in the red spectral range from optically excited InP/(Al,Ga)InP quantum dots embedded in micropillars up to 100 K. *Journal of Applied Physics*, **2011**, 110, 063108	2.5	16

62	Generation of UV laser light via intra-cavity frequency doubling of an AlGaInP-VECSEL **2011**,		1
61	InP quantum dots in pillar microcavities mode spectra and single-photon emission. *Journal of Physics: Conference Series*, **2010**, 210, 012010	0.3	2
60	InP quantum dots for applications in laser devices and future solid-state quantum gates. *Journal of Physics: Conference Series*, **2010**, 245, 012077	0.3	4
59	Smooth transition into stimulated emission of InP quantum dots based high-Q microdisk cavities. *Journal of Physics: Conference Series*, **2010**, 210, 012008	0.3	
58	Triggered single-photon emission from electrically excited quantum dots in the red spectral range. *Applied Physics Letters*, **2010**, 97, 143513	3.4	22
57	Low-density InP quantum dots embedded in Ga0.51In0.49P with high optical quality realized by a strain inducing layer. *Applied Physics Letters*, **2010**, 97, 063107	3.4	13
56	Low density MOVPE grown InGaAs QDs exhibiting ultra-narrow single exciton linewidths. *Nanotechnology*, **2010**, 21, 125606	3.4	12
55	Optical properties of red emitting self-assembled InP/(Al0.20Ga0.80)0.51In0.49P quantum dot based micropillars. *Optics Express*, **2010**, 18, 12543-51	3.3	5
54	Low threshold and room-temperature lasing of electrically pumped red-emitting InP/(Al0.20Ga0.80)0.51In0.49P quantum dots. *Journal of Physics: Conference Series*, **2010**, 210, 012009	0.3	
53	Transport of laser accelerated proton beams and isochoric heating of matter. *Journal of Physics: Conference Series*, **2010**, 244, 012009	0.3	4
52	DC and pulsed electrical excitation of single quantum dots **2010**,		1
51	MOVPE grown InGaAs quantum dots of high optical quality as seed layer for low-density InP quantum dots. *Journal of Physics: Conference Series*, **2010**, 245, 012009	0.3	
50	Optical and structural properties of InP quantum dots embedded in (AlxGa1)0.51In0.49P. *Physical Review B*, **2009**, 79,	3.3	56
49	Room-temperature lasing of electrically pumped red-emitting InP/(Al0.20Ga0.80)0.51In0.49P quantum dots embedded in a vertical microcavity. *Applied Physics Letters*, **2009**, 95, 131107	3.4	20
48	Low Threshold InP/AlGaInP Quantum Dot In-Plane Laser Emitting at 638 nm. *Applied Physics Express* , **2009**, 2, 112501	2.4	12
47	InP-quantum dots in Al0.20Ga0.80InP with different barrier configurations. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 906-909		2
46	Low threshold electrically pumped red emitting InP/Al0.20GaInP quantum dot vertical microcavity laser **2009**,		1
45	Polarization fine structure and enhanced single-photon emission of self-assembled lateral InGaAs quantum dot molecules embedded in a planar microcavity. *Journal of Applied Physics*, **2009**, 105, 122408	2.5	12

44	Electrically pumped single-photon emission in the visible spectral range up to 80 K. *Optics Express*, **2008**, 16, 12771-6	3.3	37
43	Red single-photon emission from an InP□GaInP quantum dot embedded in a planar monolithic microcavity. *Applied Physics Letters*, **2008**, 92, 071105	3.4	13
42	Pulsed layer growth of AlInGaN nanostructures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1491-1494		2
41	Red to orange electroluminescence from InP/AlGaInP quantum dots at room temperature. *Journal of Crystal Growth*, **2008**, 310, 5098-5101	1.6	4
40	Increased single-photon emission from InP/AlGaInP quantum dots grown on AlGaAs distributed Bragg reflectors. *Journal of Crystal Growth*, **2008**, 310, 4818-4820	1.6	4
39	Growth of red InP/GaInP quantum dots on a low density InAs/GaAs island seed layer by MOVPE. *Journal of Crystal Growth*, **2008**, 310, 5089-5092	1.6	1
38	Non-resonant tunneling in single pairs of vertically stacked asymmetric InP/GaInP quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1958-1960	3	2
37	Influence of the dark exciton state on the optical and quantum optical properties of single quantum dots. *Physical Review Letters*, **2008**, 101, 146402	7.4	36
36	Time- and locally resolved photoluminescence of semipolar GaInN□GaN facet light emitting diodes. *Applied Physics Letters*, **2007**, 90, 171123	3.4	18
35	Regions of Different Confinement in Low-Dimensional AlyInxGa1□□N Quantum Structures. *Advances in OptoElectronics*, **2007**, 2007, 1-6	0.5	3
34	Red to green photoluminescence of InP-quantum dots in InP. *Journal of Crystal Growth*, **2007**, 298, 595-598	1.6	22
33	Green photoluminescence of single InP-quantum dots grown on InP/AlInP distributed Bragg reflectors. *Journal of Crystal Growth*, **2007**, 298, 599-602	1.6	
32	Vertical asymmetric double quantum dots. *Journal of Crystal Growth*, **2007**, 298, 603-606	1.6	9
31	Electronic shell structure and carrier dynamics of high aspect ratio InP single quantum dots. *Physical Review B*, **2007**, 75,	3.3	30
30	Nonresonant tunneling in single asymmetric pairs of vertically stacked InP quantum dots. *Physical Review B*, **2007**, 76,	3.3	14
29	Band-gap measurements of direct and indirect semiconductors using monochromated electrons. *Physical Review B*, **2007**, 75,	3.3	82
28	Analog Modulation of 650-nm VCSELs. *IEEE Photonics Technology Letters*, **2006**, 18, 583-585	2.2	1
27	Investigations on local Ga and In incorporation of GaInN quantum wells on facets of selectively grown GaN stripes. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1587-1590		8

26	Carrier dynamics in site-controlled Ga1−xInxN quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2060-2064		1
25	Structural and optical characterization of Aly Inx Ga1−x−y N quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2073-2077		2
24	Selective growth of GaInN quantum dot structures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2005**, 26, 133-137	3	6
23	Evidence of different confinement regimes in site-controlled pyramidal InGaN structures. *Physica Status Solidi (B): Basic Research*, **2005**, 242, R97-R99	1.3	8
22	Red VCSEL for automotive applications **2005**,		1
21	Near-red emission from site-controlled pyramidal InGaN quantum dots. *Applied Physics Letters*, **2005**, 87, 163121	3.4	38
20	Single-photon emission from a type-B InP/GaInP quantum dot. *Journal of Applied Physics*, **2005**, 98, 093522	2.5	24
19	Study of as deposited metal contacts for n-SiC. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 2533-2536		1
18	Growth of self-assembled AlxInyGa1-x-yN quantum dots by MOVPE. *Journal of Crystal Growth*, **2004**, 272, 186-191	1.6	2
17	Selective growth of GaInN quantum dot structures. *Journal of Crystal Growth*, **2004**, 272, 204-210	1.6	12
16	Characterisation of quaternary AlInGaN thick layers and quantum wells grown by MOVPE. *Journal of Crystal Growth*, **2004**, 272, 386-392	1.6	13
15	Red VCSEL for high-temperature applications. *Journal of Crystal Growth*, **2004**, 272, 549-554	1.6	12
14	Optical studies of GaInP/GaP quantum dots. *Journal of Luminescence*, **2003**, 102-103, 1-6	3.8	5
13	Time-resolved and single dot spectroscopy of type II InP/GaInP quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 1197-1200		6
12	Optical studies of GaxIn1−xP/Ga0.5In0.5P quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 1225-1228		3
11	Comparison of the material properties of GaInN structures grown with ammonia and dimethyl-hydrazine as nitrogen precursors. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2145-2149		
10	160°C pulsed laser operation of AlGaInP-based vertical-cavity surface-emitting lasers. *Electronics Letters*, **2003**, 39, 1654	1.1	4
9	In-Redistribution in a GaInN Quantum Well upon Thermal Annealing. *Physica Status Solidi (B): Basic Research*, **2002**, 234, 738-741	1.3	4

8	Photoluminescence Studies on InGaN/GaN Quantum Dots. *Physica Status Solidi A*, **2002**, 192, 91-96		2
7	Laterally Coupled InGaN/GaN DFB Laser Diodes. *Physica Status Solidi A*, **2002**, 192, 301-307		10
6	Initial Experiments to Obtain Self-Assembled GaInN Quantum Islands by MOVPE. *Physica Status Solidi A*, **2002**, 192, 412-416		4
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